

ABSTRACT

METHOD FOR FORMATION OF MINIATURIZED PATTERN
AND RESIST SUBSTRATE TREATMENT SOLUTION
FOR USE IN THE METHOD

The present invention provides a method for miniaturizing a pattern without seriously increasing the production cost or impairing the production efficiency. This invention also provides a fine resist pattern and a resist substrate-treating solution used for forming the fine pattern. The pattern formation method comprises a treatment step. In the treatment step, a resist pattern after development is treated with a resist substrate-treating solution containing an amino group-containing, preferably, a tertiary polyamine-containing water-soluble polymer, so as to reduce the effective size of the resist pattern formed by the development. The present invention also relates to a resist pattern formed by that method, and further relates to a treating solution used in the method.